

80V, 119A, 3.8mΩ N-channel Power SGT MOSFET

JMSH0804MGQ

Features

- Ultra-low ON-resistance, $R_{DS(ON)}$
- Low Gate Charge
- 100% UIS Tested
- 100% ΔV_{ds} Tested
- Halogen-free; RoHS-compliant
- AEC-Q101 Qualified

Applications

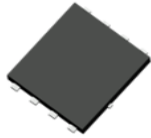
- Load Switch
- PWM Application
- General Automotive Application

Product Summary

Parameters	Value	Unit
V_{DSS}	80	V
$V_{GS(th_Typ)}$	3.0	V
$I_D(@V_{GS}=10V)$	119	A
$R_{DS(ON_Typ)}(@V_{GS}=10V)$	3.8	mΩ



Top View

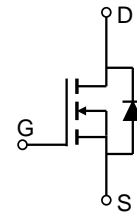


PDFN5X6-8L

Bottom View



Pin Assignment



Schematic Diagram

Ordering Information

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
JMSH0804MGQ-13	SH0804MQ	1	Tape&Reel	PDFN5x6-8L	5000	50000

Absolute Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-to-Source Voltage	80	V
V_{GS}	Gate-to-Source Voltage	± 20	V
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$	119
		$T_C = 100^\circ\text{C}$	84
I_{DM}	Pulsed Drain Current ⁽¹⁾	Refer to Fig.4	A
E_{AS}	Single Pulsed Avalanche Energy ⁽²⁾	83	mJ
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$	136
		$T_C = 100^\circ\text{C}$	68
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 175	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽³⁾	44	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.1	



**Electrical Characteristics** ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	80	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 64\text{V}$, $V_{GS} = 0\text{V}$	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	$V_{DS} = 0\text{V}$, $V_{GS} = \pm 20\text{V}$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	2.1	3.0	3.8	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance ⁽⁴⁾	$V_{GS} = 10\text{V}$, $I_D = 20\text{A}$	-	3.8	5.0	m Ω
Dynamic Characteristics						
R_g	Gate Resistance	$f = 1\text{MHz}$	-	0.7	-	Ω
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$, $V_{DS} = 40\text{V}$, $f = 1\text{MHz}$	3027	4657	6287	pF
C_{oss}	Output Capacitance		551	847	1144	pF
C_{riss}	Reverse Transfer Capacitance		-	13	50	pF
Q_g	Total Gate Charge	$V_{GS} = 0$ to 10V $V_{DS} = 40\text{V}$, $I_D = 20\text{A}$	44	68	92	nC
Q_{gs}	Gate Source Charge		16	25	34	nC
Q_{gd}	Gate Drain ("Miller") Charge		-	13	40	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{GS} = 10\text{V}$, $V_{DD} = 40\text{V}$ $I_D = 20\text{A}$, $R_{GEN} = 3\Omega$	-	22	-	ns
t_r	Turn-On Rise Time		-	30	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	37	-	ns
t_f	Turn-Off Fall Time		-	11	-	ns
Body Diode Characteristics						
I_S	Maximum Continuous Body Diode Forward Current		-	-	119	A
I_{SM}	Maximum Pulsed Body Diode Forward Current		-	-	474	A
V_{SD}	Body Diode Forward Voltage	$V_{GS} = 0\text{V}$, $I_S = 20\text{A}$	-		1.2	V
t_{rr}	Body Diode Reverse Recovery Time	$I_F = 20\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$	63	88	119	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	93	-	nC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. E_{AS} condition: Starting $T_J = 25^\circ\text{C}$, $V_{DD} = 40\text{V}$, $V_{GS} = 10\text{V}$, $R_G = 250\text{ohm}$, $L = 3\text{mH}$, $I_{AS} = 18.2\text{A}$, $V_{DD} = 0\text{V}$ during time in avalanche.
 3. $R_{\theta JA}$ is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB.
 4. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.



Typical Performance Characteristics

Figure 1: Power De-rating

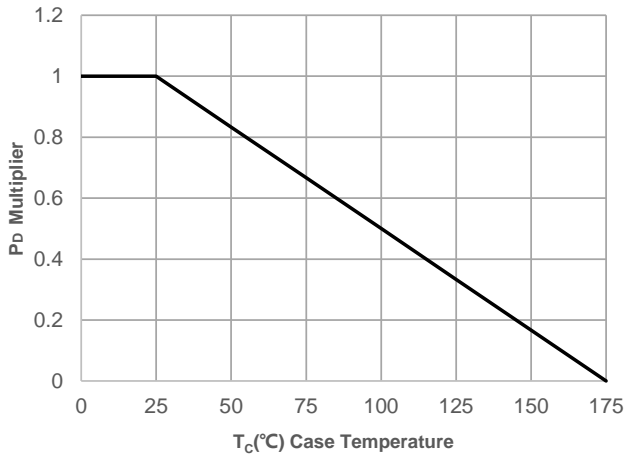


Figure 2: Current De-rating

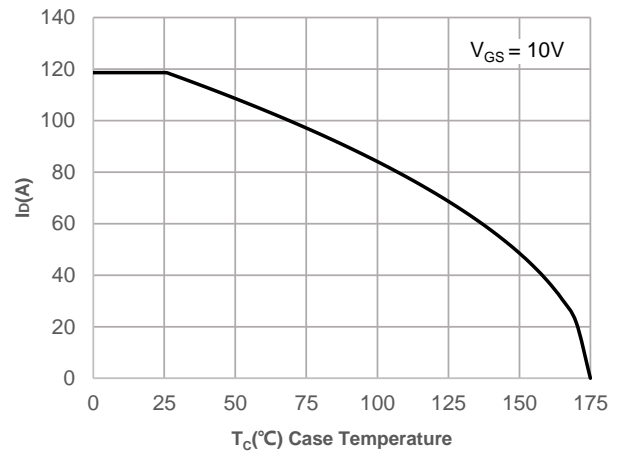


Figure 3: Normalized Maximum Transient Thermal Impedance

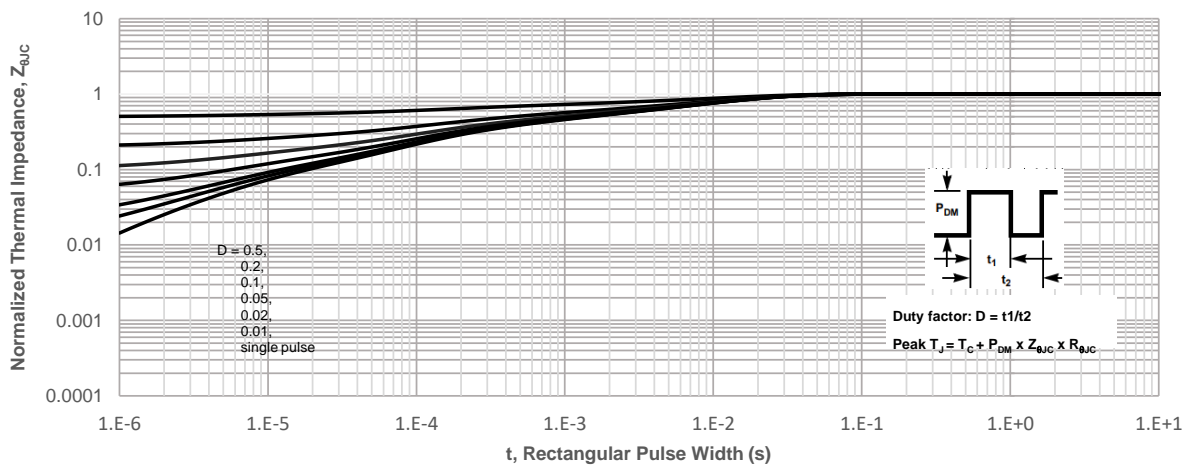
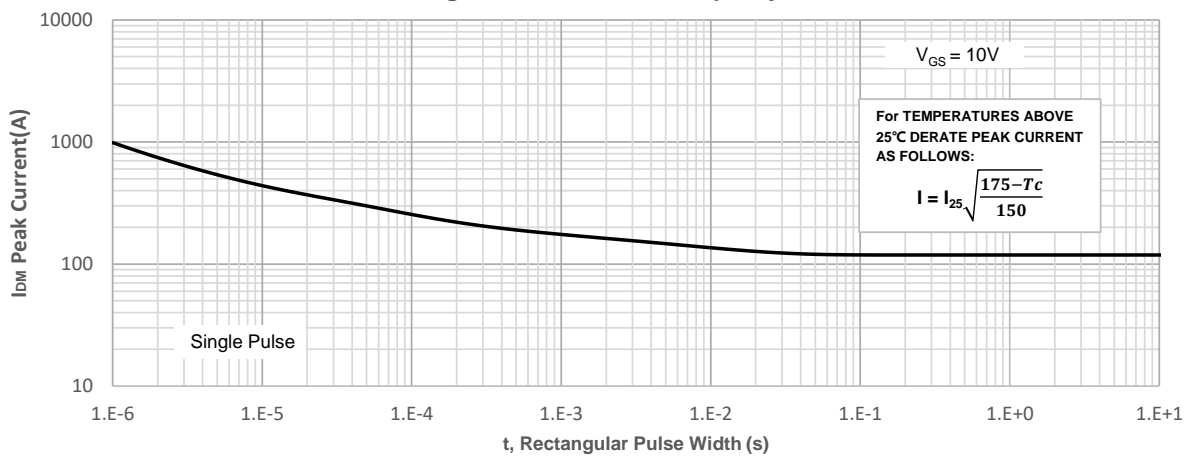
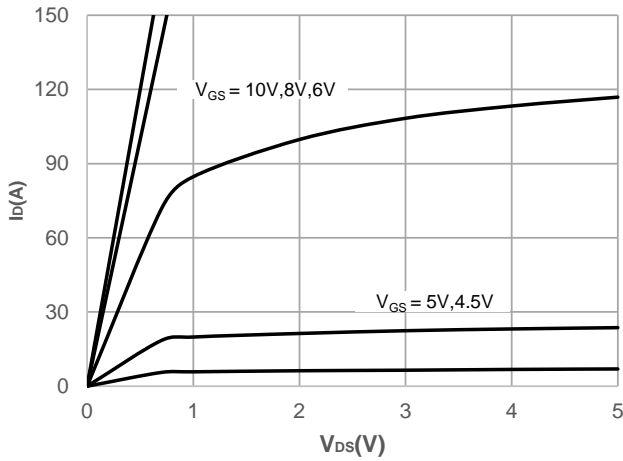
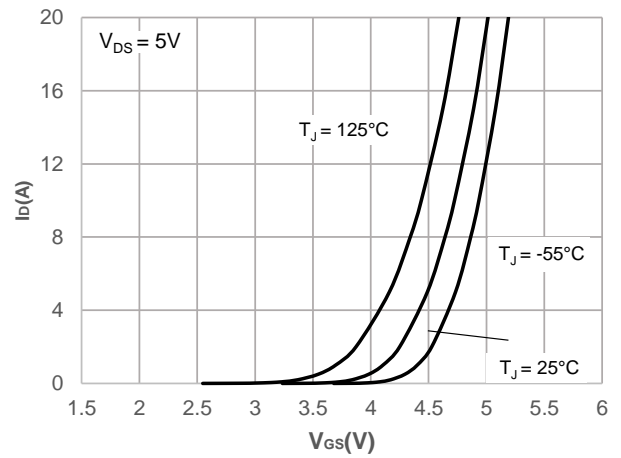
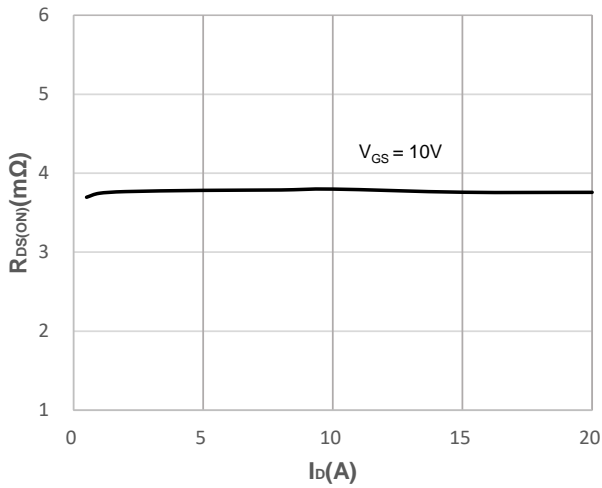
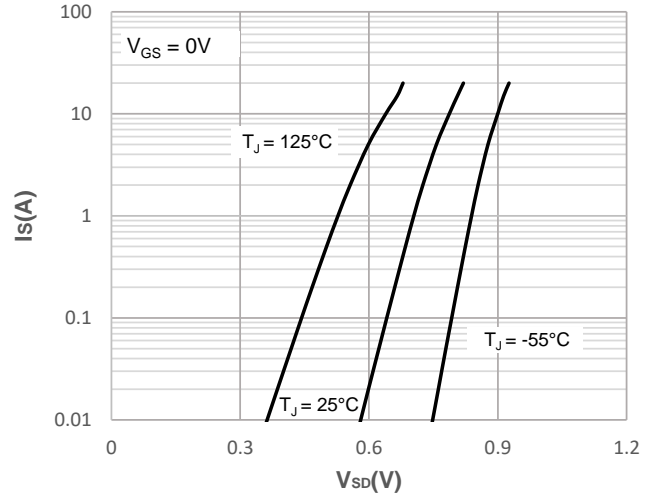
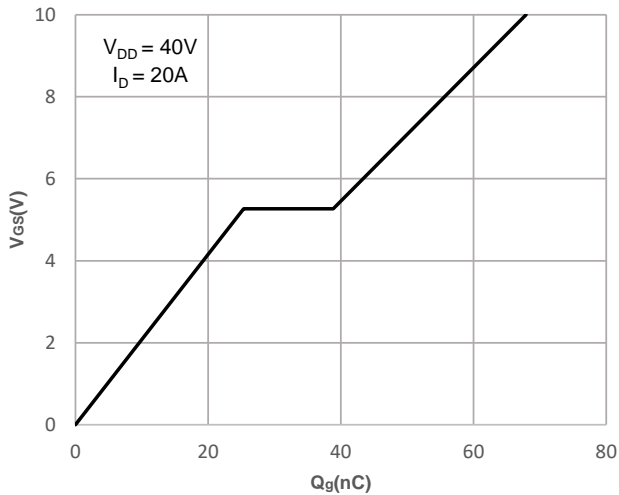
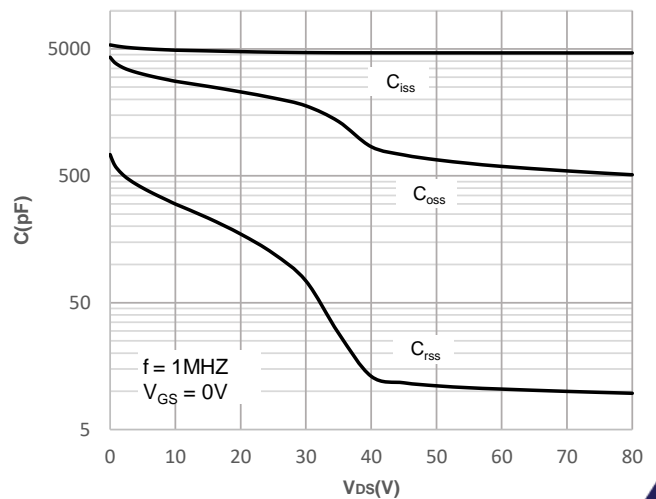


Figure 4: Peak Current Capacity



Typical Performance Characteristics

Figure 5: Output Characteristics

Figure 6: Typical Transfer Characteristics

Figure 7: On-resistance vs. Drain Current

Figure 8: Body Diode Characteristics

Figure 9: Gate Charge Characteristics

Figure 10: Capacitance Characteristics


Typical Performance Characteristics

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

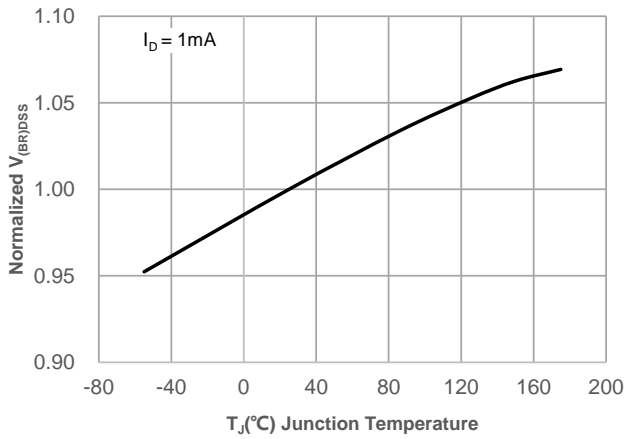


Figure 12: Normalized on Resistance vs. Junction Temperature

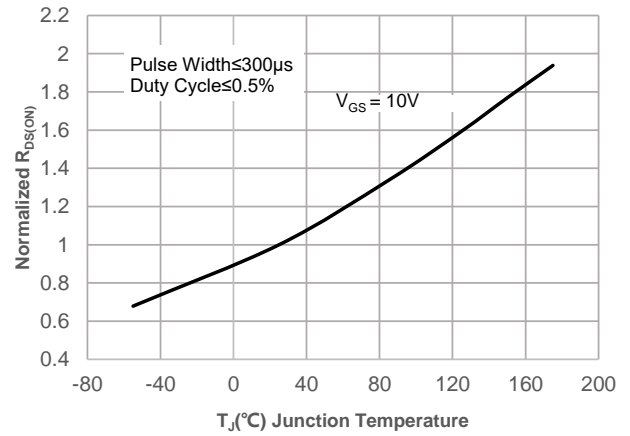


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

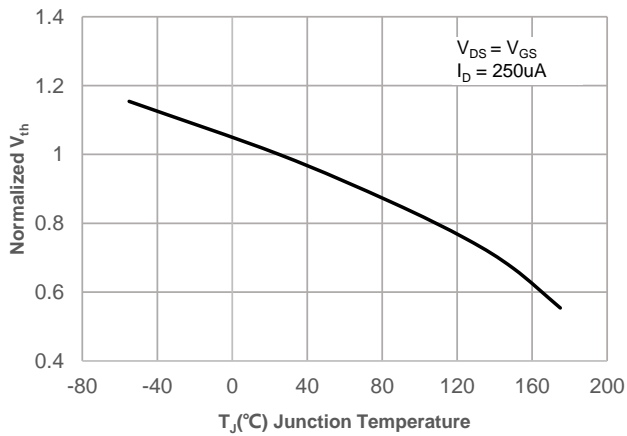


Figure 14: $R_{DS(ON)}$ vs. V_{GS}

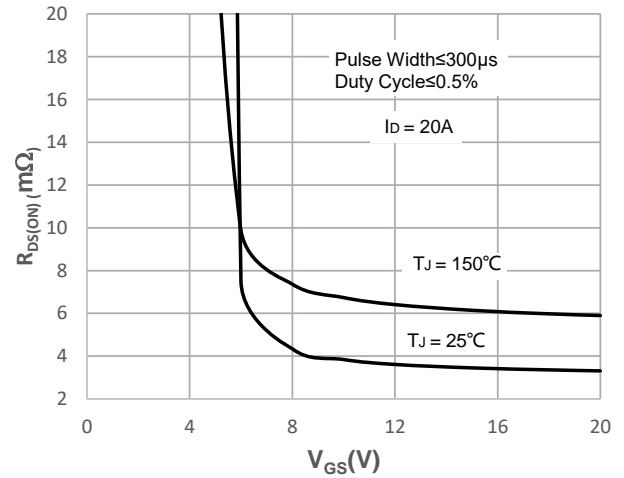
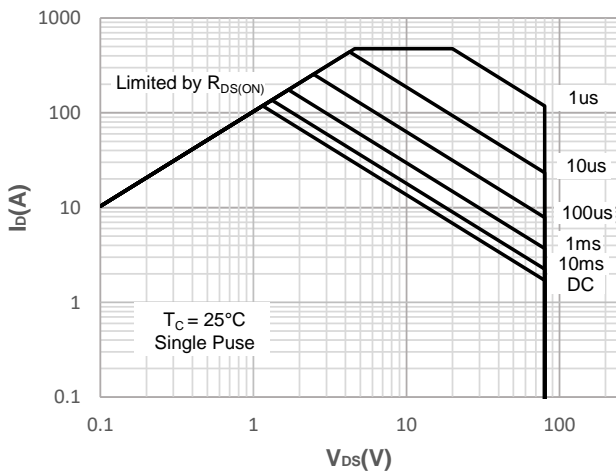


Figure 15: Maximum Safe Operating Area



Test Circuit

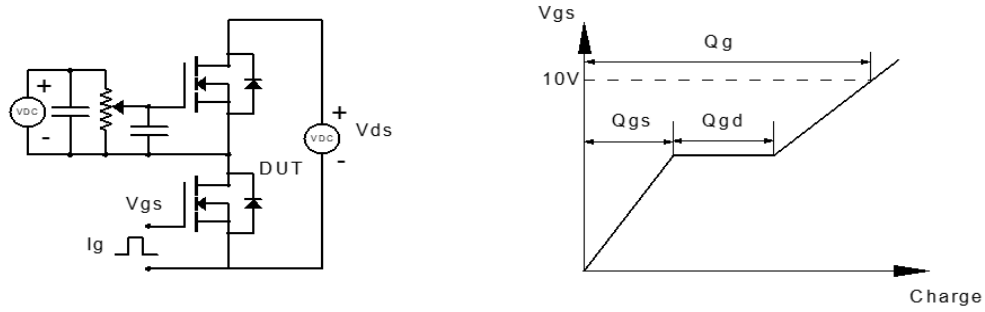


Figure 1: Gate Charge Test Circuit & Waveform

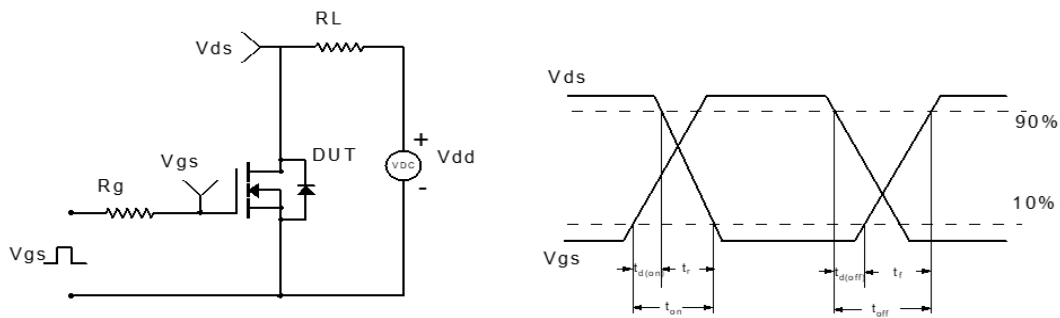


Figure 2: Resistive Switching Test Circuit & Waveform



Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

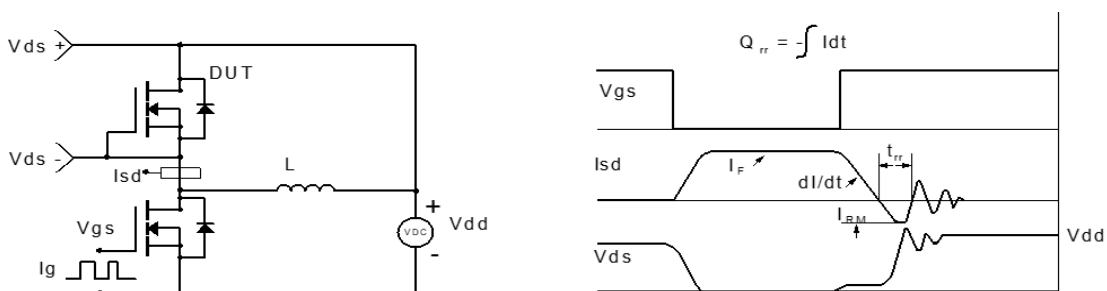
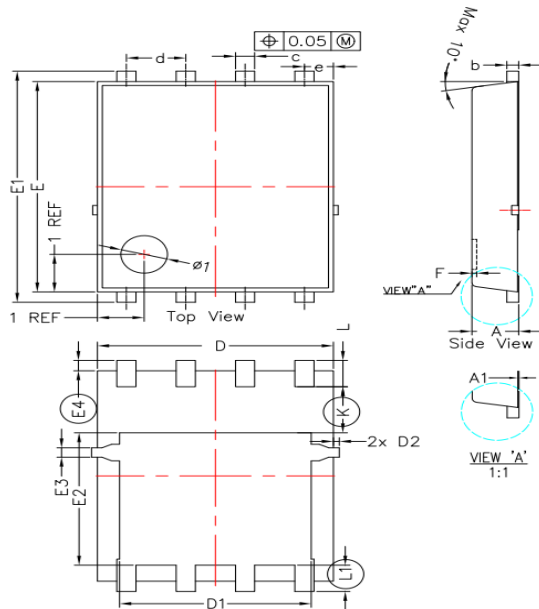


Figure 4: Diode Recovery Test Circuit & Waveform

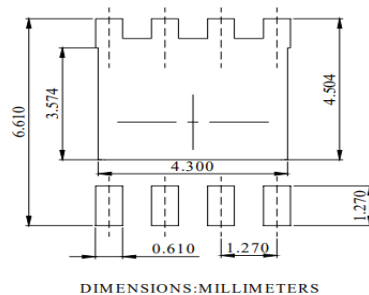


Package Mechanical Data(PDFN5X6-8L)



SYMBOLS	DIMENSION IN MM			DIMENSION IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
*A	0.900	1.000	1.150	0.035	0.039	0.045
A1	0.000	---	0.050	0.000	---	0.002
b	0.246	0.254	0.350	0.010	0.010	0.014
*C	0.310	0.410	0.510	0.012	0.016	0.020
d	1.27BSC			0.050BSC		
*D	4.950	5.050	5.150	0.195	0.199	0.203
D1	4.000	4.100	4.200	0.157	0.161	0.165
*D2	0.125REF			0.005REF		
e	0.62BSC			0.024BSC		
*E	5.500	5.600	5.700	0.217	0.220	0.224
*E1	6.050	6.150	6.250	0.238	0.242	0.246
E2	3.425	3.525	3.625	0.135	0.139	0.143
E3	0.250REF			0.010REF		
*E4	0.275REF			0.011REF		
F	-	-	0.100	-	-	0.004
*L	0.500	0.600	0.700	0.02	0.02	0.03
L1	0.600	0.700	0.800	0.02	0.03	0.03
K	1.225REF			0.05REF		

Recommended Soldering Footprint



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